

## SN65HVD5x 高输出全双工 RS-485 驱动器和接收器

### 1 特性

- 可提供 1/8 单位负载选项 (总线上多达 256 个节点)
- 总线引脚 ESD 保护超过 15 kV HBM
- 针对 1Mbps、5Mbps 和 25Mbps 信号传输速率<sup>(1)</sup> 的可选驱动器输出转换时间
- 低电流待机模式 < 1  $\mu$ A
- 无干扰上电和下电总线 I/O
- 总线空闲、开路和短路失效防护
- 设计用于 RS-422 和 RS-485 网络
- 提供 3.3V 器件, SN65HVD30-35<sup>1</sup>

### 2 应用

- 公用事业计量表
- 机箱至机箱互联
- DTE/DCE 接口
- 工业、工艺和楼宇自动化
- 销售点 (POS) 终端和网络

### 3 说明

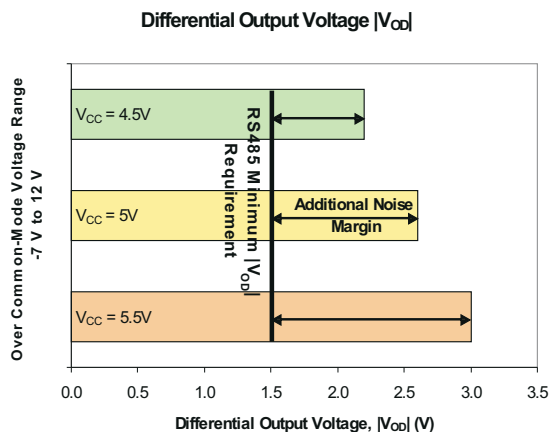
SN65HVD5X 器件是采用 5V 电源供电的三态差分线路驱动器和差分输入线路接收器。每个驱动器和接收器都具有用于全双工总线通信设计的独立输入和输出引脚。它们专为平衡传输线路而设计, 可与符合 ANSI TIA/EIA-485A、TIA/EIA-422-B、ITU-T v.11 和 ISO 8482:1993 标准的器件进行互操作。

SN65HVD50、SN65HVD51 和 SN65HVD52 均完全启用, 无需外部的使能引脚。

SN65HVD53、SN65HVD54 和 SN65HVD55 均具有高电平有效的驱动器使能端和低电平有效的接收器使能端。禁用驱动器和接收器后可获得低于 1  $\mu$ A 的低待机电流。

所有器件的工作温度范围是 -40°C 至 85°C。

与典型的 RS-485 驱动器相比, SN65HVD5x 的高输出特性可提供更高的噪声容限。额外的噪声容限使得长电缆和恶劣噪声环境中的应用成为可能。



<sup>1</sup> 线路的信号传输速率是每秒进行电压转换的次数, 以单位 bps (每秒位数) 来表示。



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## 4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision E (October 2009) to Revision F (March 2023)	Page
• Changed the <i>Thermal Characteristics</i> table.....	11
• Changed the <i>Typical Characteristics</i> .....	12

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Changes from Revision D (June 2008) to Revision E (October 2009)	Page
• 将特性要点的文本从“提供 3.3V 器件，SN65HVD30-39”更改为“提供 3.3V 器件，SN65HVD30-35” .....	1
• 删除了整个数据表中对 SN65HVD56、SN65HVD57、SN65HVD58、SN65HVD59 的所有引用.....	1
• Deleted RECEIVER EQUALIZATION CHARACTERISTICS from the data sheet.....	4
• Changed scale of 图 7-6 .....	12
• Changed scale of 图 7-7 .....	12
• Added 图 7-11 .....	12
• Changed 图 10-1 .....	22

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Changes from Revision C (July 2006) to Revision D (June 2008)	Page
• 将特性要点的文本从“符合或超出 ANSI TIA/EIA-485-A 的要求并兼容 RS-422”更改为“设计用于 RS-422 和 RS-485 网络” .....	1

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Changes from Revision B (May 2006) to Revision C (July 2006)	Page
• Added 图 7-10 .....	12
• Added 图 7-12 .....	12

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Changes from Revision A (February 2006) to Revision B (May 2006)	Page
• Added $t_{sk(p)}$ TYP Values.....	8
• Deleted $t_{sk(p)}$ MAX Values.....	8

<b>Changes from Revision * (September 2005) to Revision A (February 2006)</b>	<b>Page</b>
• 更改了说明和图示.....	1
• Changed device SN65HVD50, 51, and 52 SOIC Markings From Preview To 65HVD50, 65HVD51, and 65HVD52 .....	4
• Changed $V_{OD(RING)}$ Max value From $0.05 V_{OD(SS)} $ To: 10% with the associated note.....	7
• Changed $t_f$ MIN value From: 25 ns To: 20 ns.....	8
• Changed $t_f$ MIN value From: 25 ns To: 20 ns.....	8
• Changed Supply Current - HVD50 MAX value From 8 mA To: 2.7 mA.....	9
• Changed section LOW-POWER SHUTDOWN MODE To: LOW-POWER STANDBY MODE.....	19

## 5 Available Options

SIGNALING RATE	UNIT LOADS	ENABLES	BASE PART NUMBER	SOIC MARKING
25 Mbps	1/2	No	SN65HVD50	65HVD50
5 Mbps	1/8	No	SN65HVD51	65HVD51
1 Mbps	1/8	No	SN65HVD52	65HVD52
25 Mbps	1/2	Yes	SN65HVD53	65HVD53
5 Mbps	1/8	Yes	SN65HVD54	65HVD54
1 Mbps	1/8	Yes	SN65HVD55	65HVD55

## 6 Pin Configurations

D PACKAGE (TOP VIEW)

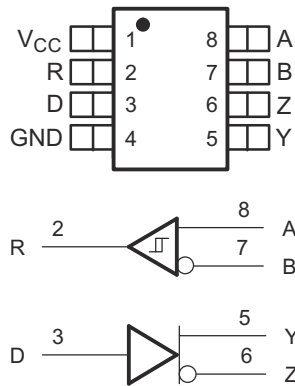


图 6-1. SN65HVD50, SN65HVD51, SN65HVD52

D PACKAGE (TOP VIEW)

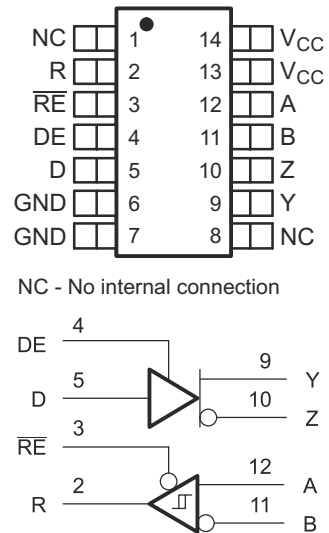


图 6-2. SN65HVD53, SN65HVD54, SN65HVD55

## 7 Specifications

### 7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1) (2)</sup>

		UNIT
$V_{CC}$	Supply voltage range	- 0.3 V to 6 V
$V_{(A)}, V_{(B)}, V_{(Y)}, V_{(Z)}$	Voltage range at any bus terminal (A, B, Y, Z)	- 9 V to 14 V
$V_{(TRANS)}$	Voltage input, transient pulse through 100 $\Omega$ . See <a href="#">图 8-12 (A, B, Y, Z)</a> <sup>(3)</sup>	- 50 to 50 V
$V_I$	Voltage input range (D, DE, RE)	-0.5 V to 7 V
$P_{D(cont)}$	Continuous total power dissipation	Internally limited <sup>(4)</sup>
$I_O$	Output current (receiver output only, R)	11 mA

- (1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.
- (3) This tests survivability only and the output state of the receiver is not specified.
- (4) The thermal shutdown typically occurs when the junction temperature reaches 165°C.

### 7.2 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
$V_{CC}$	Supply voltage		4.5		5.5	V
$V_I$ or $V_{IC}$	Voltage at any bus terminal (separately or common mode)		- 7 <sup>(1)</sup>		12	
$1/t_{UI}$	Signaling rate	SN65HVD50, SN65HVD53			25	Mbps
		SN65HVD51, SN65HVD54			5	
		SN65HVD52, SN65HVD55			1	
$R_L$	Differential load resistance		54	60		$\Omega$
$V_{IH}$	High-level input voltage	D, DE, RE	2		$V_{CC}$	V
$V_{IL}$	Low-level input voltage	D, DE, RE	0		0.8	
$V_{ID}$	Differential input voltage		-12		12	
$I_{OH}$	High-level output current	Driver	-60			
		Receiver	- 8			
$I_{OL}$	Low-level output current	Driver			60	mA
		Receiver			8	
$T_J$ <sup>(2)</sup>	Junction temperature		- 40		150	°C

- (1) The algebraic convention, in which the least positive (most negative) limit is designated as minimum is used in this data sheet.
- (2) See thermal characteristics table for information regarding this specification.

### 7.3 Electrostatic Discharge Protection

PARAMETER	TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
Human body model	Bus terminals and GND		$\pm 16$		kV
Human body model <sup>(2)</sup>	All pins		$\pm 4$		
Charged-device-model <sup>(3)</sup>	All pins		$\pm 1$		

- (1) All typical values at 25°C and with a 5-V supply.
- (2) Tested in accordance with JEDEC Standard 22, Test Method A114-A.
- (3) Tested in accordance with JEDEC Standard 22, Test Method C101.

## 7.4 Driver Electrical Characteristics

over recommended operating conditions unless otherwise noted

PARAMETER		TEST CONDITIONS		MIN	TYP <sup>(1)</sup>	MAX	UNIT	
$V_{I(K)}$	Input clamp voltage	$I_I = -18 \text{ mA}$		-1.5			V	
$ V_{OD(SS)} $	Steady-state differential output voltage	$I_O = 0$		4		$V_{CC}$		
		$R_L = 54 \Omega$ , See 图 8-1 (RS-485)		1.7	2.6			
		$R_L = 100 \Omega$ , See 图 8-1 (RS-422)		2.4	3.2			
		$V_{\text{test}} = -7 \text{ V to } 12 \text{ V}$ , See 图 8-2		1.6				
$\Delta  V_{OD(SS)} $	Change in magnitude of steady-state differential output voltage between states	$R_L = 54 \Omega$ , See 图 8-1 and 图 8-2		-0.2		0.2		
$V_{OD(RING)}$	Differential Output Voltage overshoot and undershoot	$R_L = 54 \Omega$ , $C_L = 50 \text{ pF}$ , See 图 8-5 See 图 8-3 for definition				10% <sup>(2)</sup>		
$V_{OC(PP)}$	Peak-to-peak common-mode output voltage	HVD50, HVD53			0.5			
		HVD51, HVD54		See 图 8-4	0.4			
		HVD52, HVD55			0.4			
$V_{OC(SS)}$	Steady-state common-mode output voltage	See 图 8-4		2.2		3.3		
$\Delta V_{OC(SS)}$	Change in steady-state common-mode output voltage			-0.1		0.1		
$I_{Z(Z)}$ or $I_{Y(Z)}$	High-impedance state output current	HVD50, HVD51, HVD52	$V_{CC} = 0 \text{ V}$ , $V_Z$ or $V_Y = 12 \text{ V}$ , Other input at 0 V			90	$\mu\text{A}$	
			$V_{CC} = 0 \text{ V}$ , $V_Z$ or $V_Y = -7 \text{ V}$ , Other input at 0 V		-10			
		HVD53, HVD54, HVD55	$V_{CC} = 5 \text{ V or } 0 \text{ V}$ , $DE = 0 \text{ V}$ $V_Z$ or $V_Y = 12 \text{ V}$	Other input at 0 V				90
			$V_{CC} = 5 \text{ V or } 0 \text{ V}$ , $DE = 0 \text{ V}$ $V_Z$ or $V_Y = -7 \text{ V}$			-10		
$I_{Z(S)}$ or $I_{Y(S)}$	Short-circuit output current <sup>(3)</sup>	$V_Z$ or $V_Y = -7 \text{ V}$		Other input at 0 V	-250	250	mA	
		$V_Z$ or $V_Y = 12 \text{ V}$			-250	250		
$I_I$	Input current	D, DE		0		100	$\mu\text{A}$	
$C_{(OD)}$	Differential output capacitance	$V_{OD} = 0.4 \sin(4E6 \pi t) + 0.5 \text{ V}$ , DE at 0 V			16		pF	

(1) All typical values are at 25°C and with a 5-V supply.

(2) 10% of the peak-to-peak differential output voltage swing, per TIA/EIA-485

(3) Under some conditions of short-circuit to negative voltages, output currents exceeding the ANSI TIA/EIA-485-A maximum current of 250 mA may occur. Continuous exposure may affect device reliability.

## 7.5 Driver Switching Characteristics

over recommended operating conditions unless otherwise noted

PARAMETER		TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
t <sub>PLH</sub>	Propagation delay time, low-to-high-level output	HVD50, HVD53	4	8	12	ns
		HVD51, HVD54	20	29	46	
		HVD52, HVD55	90	143	230	
t <sub>PHL</sub>	Propagation delay time, high-to-low-level output	HVD50, HVD53	4	8	12	ns
		HVD51, HVD54	20	30	46	
		HVD52, HVD55	90	143	230	
t <sub>r</sub>	Differential output signal rise time	HVD50, HVD53	3	6	12	ns
		HVD51, HVD54	20	34	60	
		HVD52, HVD55	120	197	300	
t <sub>f</sub>	Differential output signal fall time	HVD50, HVD53	3	6	11	ns
		HVD51, HVD54	20	33	60	
		HVD52, HVD55	120	192	300	
t <sub>sk(p)</sub>	Pulse skew ( t <sub>PHL</sub> - t <sub>PLH</sub>  )	HVD50, HVD53		1.4		ns
		HVD51, HVD54		1.6		
		HVD52, HVD55		7.4		
t <sub>sk(pp)</sub> <sup>(2)</sup>	Part-to-part skew	HVD50, HVD53		1		ns
		HVD51, HVD54		4		
		HVD52, HVD55		22		
t <sub>PZH1</sub>	Propagation delay time, high-impedance-to-high-level output	HVD53			30	ns
		HVD54			180	
		HVD55			380	
t <sub>PHZ</sub>	Propagation delay time, high-level-to-high-impedance output	HVD53			16	ns
		HVD54			40	
		HVD55			110	
t <sub>PZL1</sub>	Propagation delay time, high-impedance-to-low-level output	HVD53			23	ns
		HVD54			200	
		HVD55			420	
t <sub>PLZ</sub>	Propagation delay time, low-level-to-high-impedance output	HVD53			19	ns
		HVD54			70	
		HVD55			160	
t <sub>PZH2</sub>	Propagation delay time, standby-to-high-level output	R <sub>L</sub> = 110 Ω, $\overline{RE}$ at 3 V, See 图 8-6 D = 3 V and S1 = Y, D = 0 V and S1 = Z			3300	ns
t <sub>PZL2</sub>	Propagation delay time, standby-to-low-level output	R <sub>L</sub> = 110 Ω, $\overline{RE}$ at 3 V, See 图 8-7 D = 3 V and S1 = Z, D = 0 V and S1 = Y			3300	ns

(1) All typical values are at 25°C and with a 5-V supply.

(2) t<sub>sk(pp)</sub> is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.



## 7.6 Receiver Electrical Characteristics

over recommended operating conditions unless otherwise noted

PARAMETER		TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT	
$V_{IT+}$	Positive-going differential input threshold voltage	$I_O = -8 \text{ mA}$			-0.02	V	
$V_{IT-}$	Negative-going differential input threshold voltage	$I_O = 8 \text{ mA}$	-0.2				
$V_{hys}$	Hysteresis voltage ( $V_{IT+} - V_{IT-}$ )			50		mV	
$V_{IK}$	Enable-input clamp voltage	$I_I = -18 \text{ mA}$	-1.5			V	
$V_O$	Output voltage	$V_{ID} = 200 \text{ mV}$ , $I_O = -8 \text{ mA}$ , See <a href="#">图 8-8</a>	4			V	
		$V_{ID} = -200 \text{ mV}$ , $I_O = 8 \text{ mA}$ , See <a href="#">图 8-8</a>			0.3		
$I_{O(Z)}$	High-impedance-state output current	$V_O = 0$ or $V_{CC}$ RE at $V_{CC}$	-1		1	$\mu\text{A}$	
$I_A$ or $I_B$	Bus input current	HVD50, HVD53	$V_A$ or $V_B = 12 \text{ V}$	Other input at 0 V	0.19	0.3	mA
			$V_A$ or $V_B = 12 \text{ V}$ , $V_{CC} = 0 \text{ V}$		0.24	0.4	
			$V_A$ or $V_B = -7 \text{ V}$		-0.35	-0.19	
			$V_A$ or $V_B = -7 \text{ V}$ , $V_{CC} = 0 \text{ V}$		-0.25	-0.14	
		HVD51, HVD52, HVD54, HVD55	$V_A$ or $V_B = 12 \text{ V}$	Other input at 0 V	0.05	0.1	mA
			$V_A$ or $V_B = 12 \text{ V}$ , $V_{CC} = 0 \text{ V}$		0.06	0.1	
			$V_A$ or $V_B = -7 \text{ V}$		-0.1	-0.05	
			$V_A$ or $V_B = -7 \text{ V}$ , $V_{CC} = 0 \text{ V}$		-0.1	-0.03	
$I_{IH}$	Input current, RE	$V_{IH} = 2 \text{ V}$	-60			$\mu\text{A}$	
		$V_{IL} = 0.8 \text{ V}$	-60			$\mu\text{A}$	
$C_{ID}$	Differential input capacitance	$V_{ID} = 0.4 \sin(4E6 \pi t) + 0.5 \text{ V}$ , DE at 0 V		16		pF	
<b>Supply Current</b>							
$I_{CC}$	Supply current	HVD50	D at 0 V or $V_{CC}$ and No Load		2.7	mA	
					8		
		HVD53	RE at 0 V, D at 0 V or $V_{CC}$ , DE at 0 V, No load (Receiver enabled and driver disabled)		2.3	mA	
					2.9		
		HVD53, HVD54, HVD55	RE at $V_{CC}$ , D at $V_{CC}$ , DE at 0 V, No load (Receiver disabled and driver disabled)		0.08	1	$\mu\text{A}$
		HVD53	RE at 0 V, D at 0 V or $V_{CC}$ , DE at $V_{CC}$ , No load (Receiver enabled and driver enabled)		2.7	mA	
					8		
HVD53	RE at $V_{CC}$ , D at 0 V or $V_{CC}$ , DE at $V_{CC}$ No load (Receiver disabled and driver enabled)		2.3	mA			
			7.7				

(1) All typical values are at 25°C and with a 5-V supply.

## 7.7 Receiver Switching Characteristics

over recommended operating conditions unless otherwise noted

PARAMETER		TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT		
t <sub>PLH</sub>	Propagation delay time, low-to-high-level output	HVD50, HVD53		24	40	ns		
		HVD51, HVD52, HVD54, HVD55		43	55			
t <sub>PHL</sub>	Propagation delay time, high-to-low-level output	HVD50, HVD53		26	35			
		HVD51, HVD52, HVD54, HVD55		47	60			
t <sub>sk(p)</sub>	Pulse skew ( t <sub>PHL</sub> - t <sub>PLH</sub>  )	HVD50, HVD53	V <sub>ID</sub> = -1.5 V to 1.5 V, C <sub>L</sub> = 15 pF, See <a href="#">图 8-9</a>				5	
		HVD51, HVD54					7	
t <sub>sk(pp)</sub> <sup>(2)</sup>	Part-to-part skew	HVD50, HVD53			5			
		HVD51, HVD54			6			
		HVD52, HVD55			6			
t <sub>r</sub>	Output signal rise time				2.3		4	
t <sub>f</sub>	Output signal fall time				2.4		4	
t <sub>PHZ</sub>	Output disable time from high level	DE at 3 V, C <sub>L</sub> = 15 pF						17
t <sub>PZH1</sub>	Output enable time to high level	See <a href="#">图 8-10</a>						10
t <sub>PZH2</sub>	Propagation delay time, standby-to-high-level output	DE at 0 V, C <sub>L</sub> = 15 pF See <a href="#">图 8-10</a>						3300
t <sub>PLZ</sub>	Output disable time from low level	DE at 3 V, C <sub>L</sub> = 15 pF					13	
t <sub>PZL1</sub>	Output enable time to low level	See <a href="#">图 8-11</a>					10	
t <sub>PZL2</sub>	Propagation delay time, standby-to-low-level output	DE at 0 V, C <sub>L</sub> = 15 pF See <a href="#">图 8-11</a>					3300	

(1) All typical values are at 25°C and with a 5-V supply

(2) t<sub>sk(pp)</sub> is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

## 7.8 Thermal Characteristics

over operating free-air temperature range unless otherwise noted<sup>(1)</sup>

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$\theta_{JA}$	Junction-to-ambient thermal resistance	Low-K board	HVD51	230.8		°C/W
			HVD53, HVD54, HVD55, HVD52, HVD50	-		
	Junction-to-ambient thermal resistance	High-K board	HVD51	135.1		
			HVD50, HVD52	116.7		
$\theta_{JB}$	Junction-to-board thermal resistance	High-K board	HVD53, HVD54, HVD55	93.2		
			HVD51	44.4		
			HVD50, HVD52	63.4		
$\theta_{JC}$	Junction-to-case thermal resistance	No board	HVD53, HVD54, HVD55	49.4		
			HVD51	43.5		
			HVD50, HVD52	56.3		
$P_D$	Device power dissipation	$R_L = 60\Omega$ , $C_L = 50$ pF, Input to D a 50% duty cycle square wave at indicated signaling rate	HVD51	47.5		mW
			HVD50 (25Mbps)	420		
			HVD52 (1Mbps)	383		
		$R_L = 60\Omega$ , $C_L = 50$ pF, DE at $V_{CC}$ $\overline{RE}$ at 0 V, Input to D a 50% duty cycle square wave at indicated signaling rate	HVD53 (25Mbps)	420		
			HVD54 (10Mbps)	404		
			HVD55 (1Mbps)	383		
$T_A$	Ambient air temperature	Low-K board, No airflow	HVD50	- 40	55	°C
			HVD51, HVD52	- 40	84	
			HVD53, HVD54, HVD55	- 40	85	
		High-K board, No airflow	HVD50, HVD51, HVD52	- 40	85	
			HVD53, HVD54, HVD55	- 40	85	
$T_{JSD}$	Thermal shutdown junction temperature			165		

(1) See *Application Information* section for an explanation of these parameters.

## 7.9 Typical Characteristics

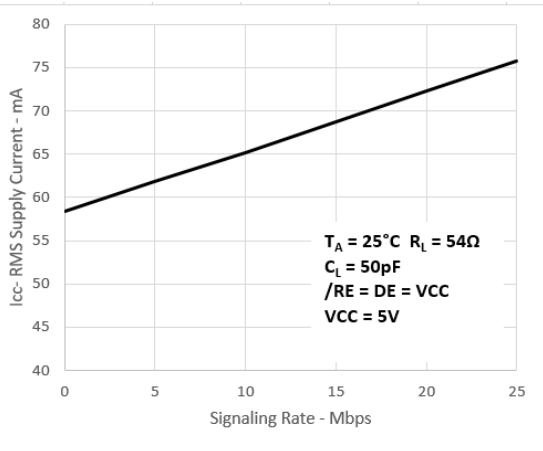


图 7-1. HVD50, HVD53 RMS Supply Current vs Signaling Rate

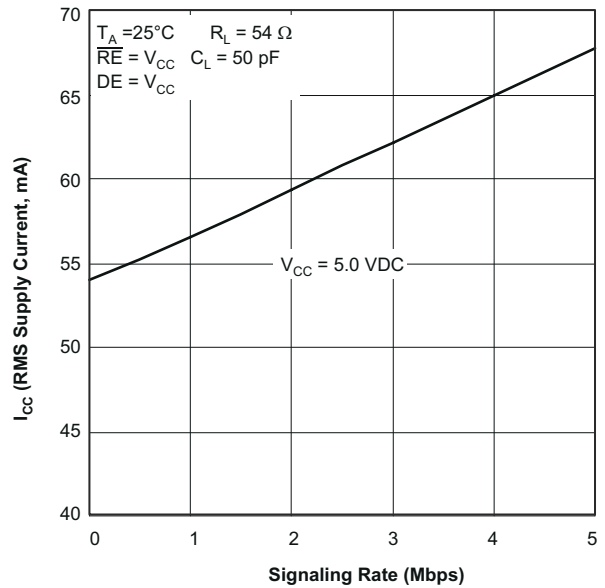


图 7-2. HVD51, HVD54 RMS Supply Current vs Signaling Rate

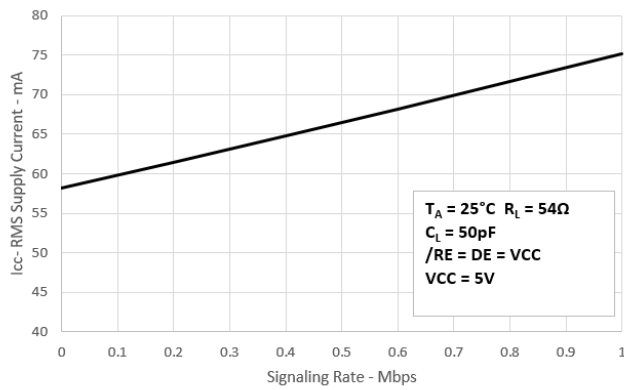


图 7-3. HVD52, HVD55 RMS Supply Current vs Signaling Rate

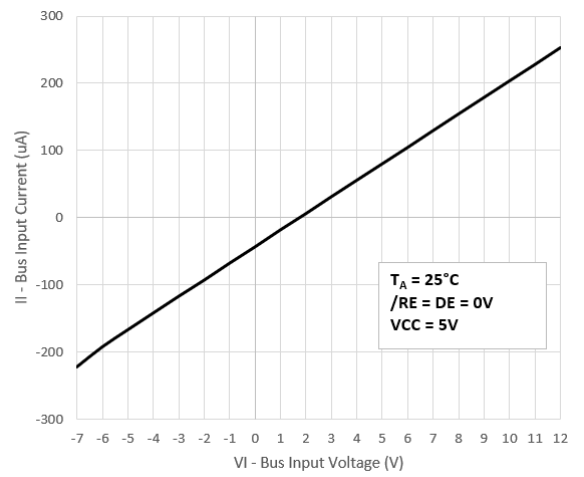


图 7-4. HVD50, HVD53 BUS Input Current vs Input Voltage

### 7.9 Typical Characteristics (continued)

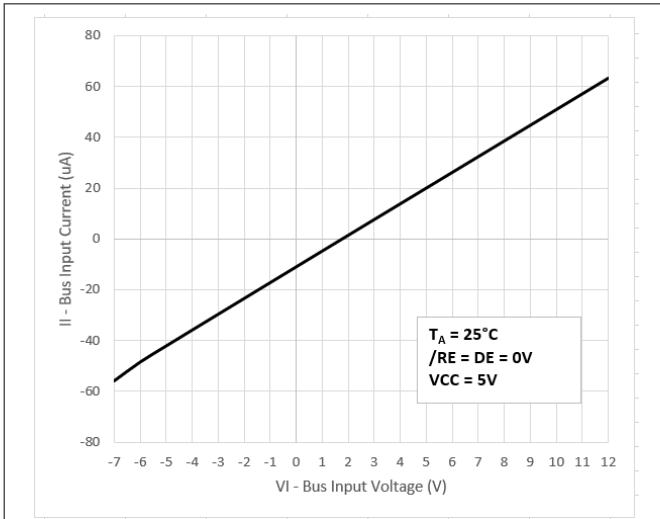


图 7-5. HVD51, HVD52, HVD54, HVD55 BUS Input Current vs Input Voltage

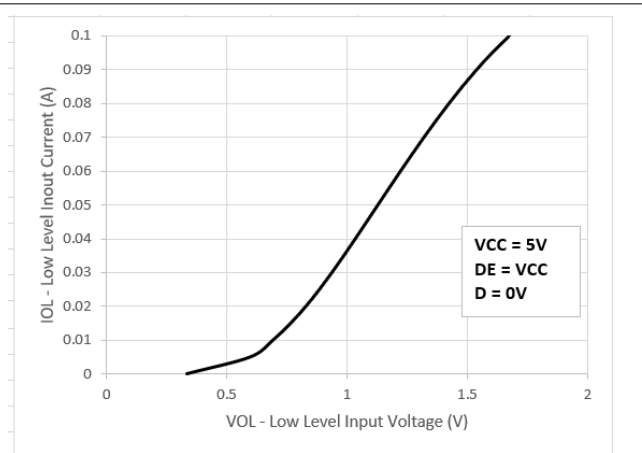


图 7-6. Driver LOW-Level Output Current vs Low-Level Output Voltage

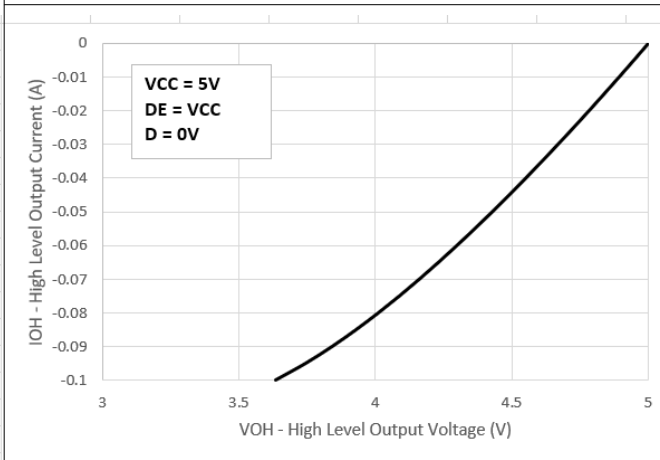


图 7-7. Driver High-Level Output Current vs High-Level Output Voltage

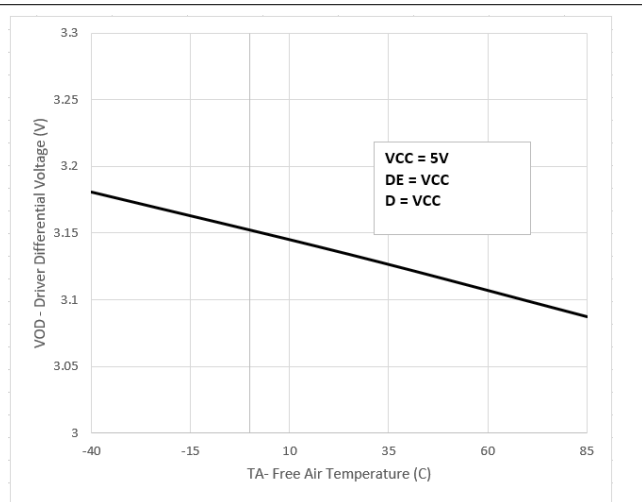


图 7-8. Driver Differential Output Voltage vs Free-Air Temperature

### 7.9 Typical Characteristics (continued)

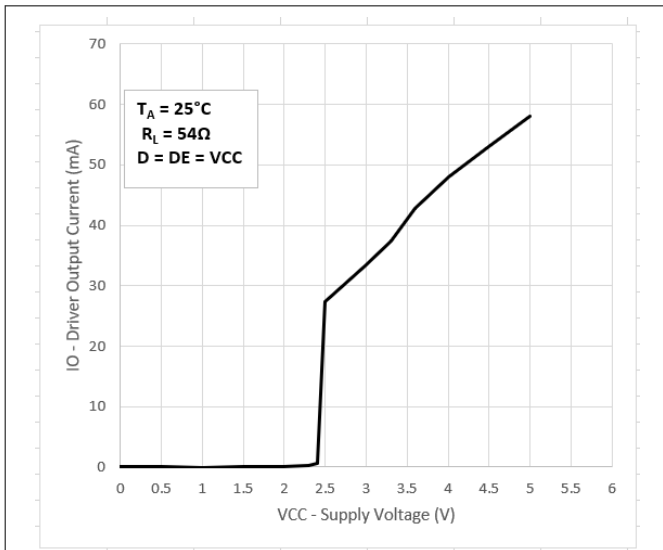


图 7-9. Driver Output Current vs Supply Voltage

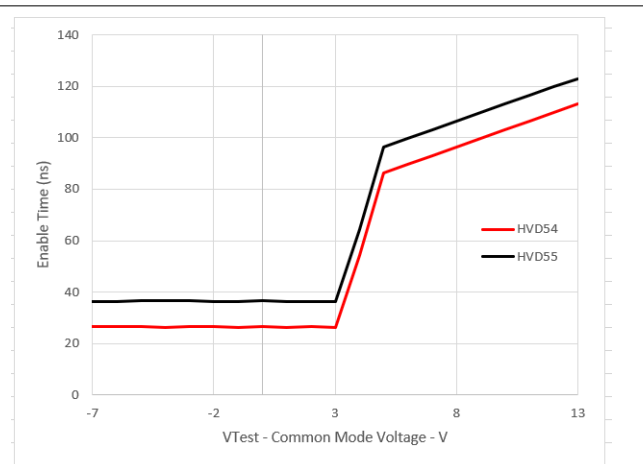


图 7-10. Enable Time vs Common-Mode Voltage  
 (See 图 7-12)

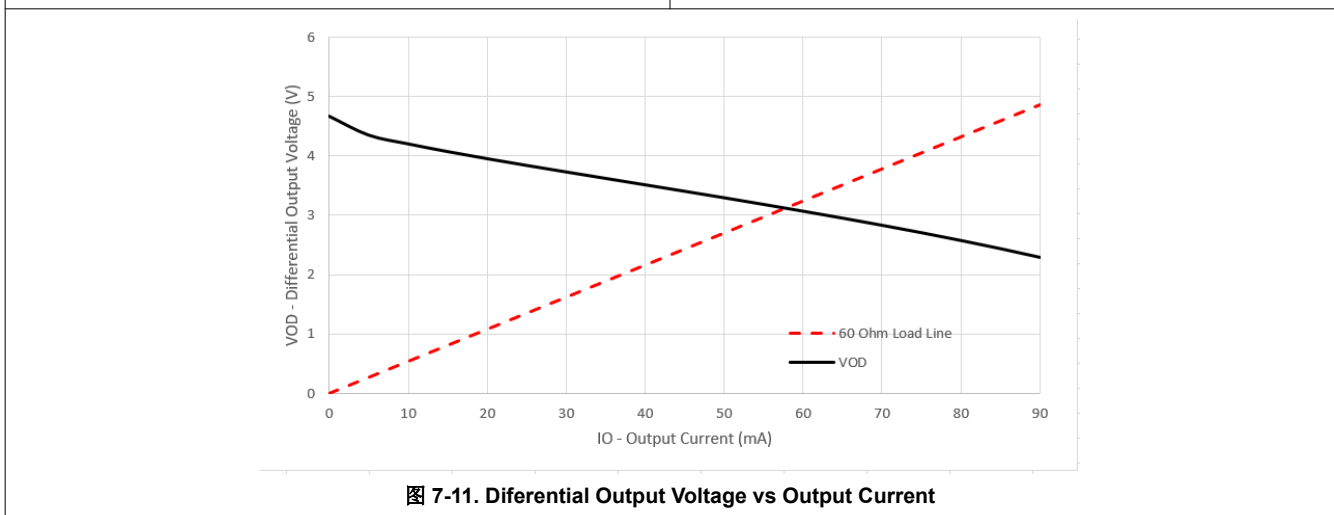
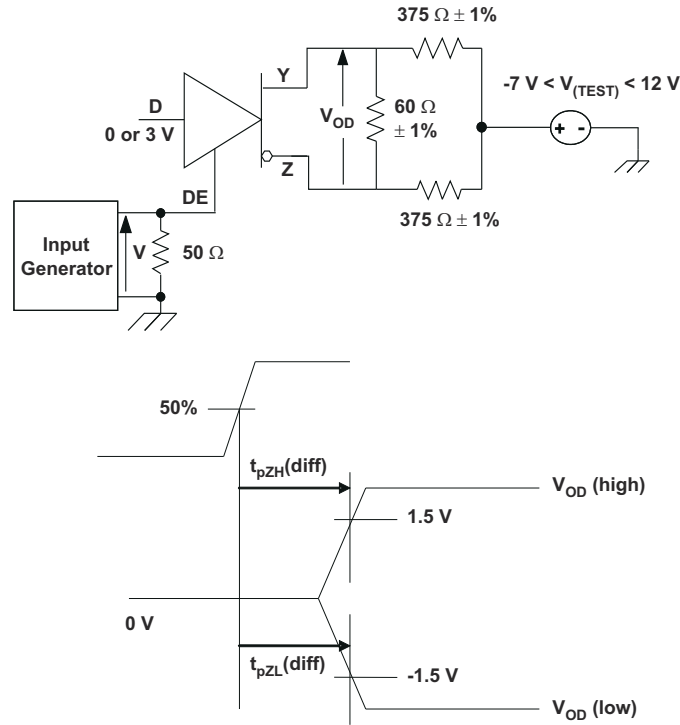


图 7-11. Diferential Output Voltage vs Output Current

### 7.9 Typical Characteristics (continued)



1. The time  $t_{pZL}(x)$  is the measure from DE to  $V_{OD}(x)$ .  $V_{OD}$  is valid when it is greater than 1.5 V.

图 7-12. Driver Enable Time From DE to  $V_{OD}$

## 8 Parameter Measurement Information

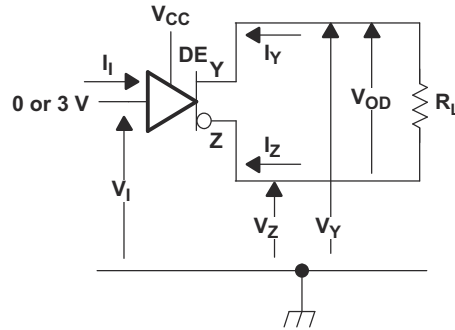


图 8-1. Driver  $V_{OD}$  Test Circuit: Voltage and Current Definitions

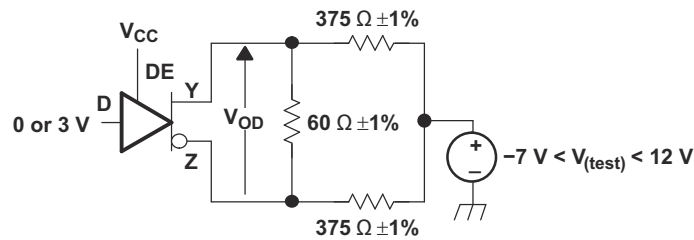


图 8-2. Driver  $V_{OD}$  With Common-Mode Loading Test Circuit

$V_{OD(RING)}$  is measured at four points on the output waveform, corresponding to overshoot and undershoot from the  $V_{OD(H)}$  and  $V_{OD(L)}$  steady state values.

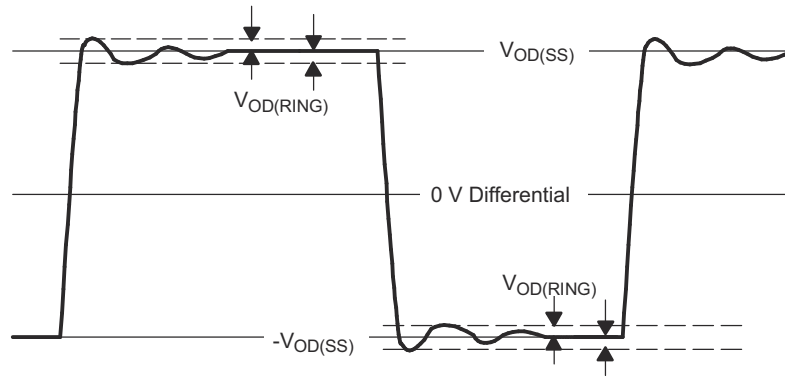
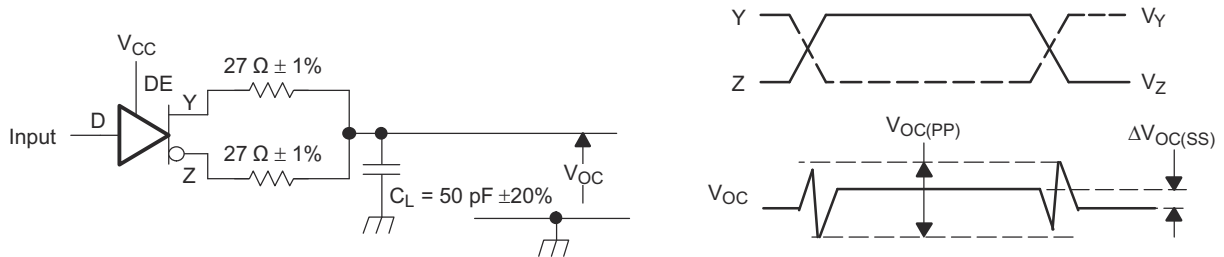


图 8-3.  $V_{OD(RING)}$  Waveform and Definitions

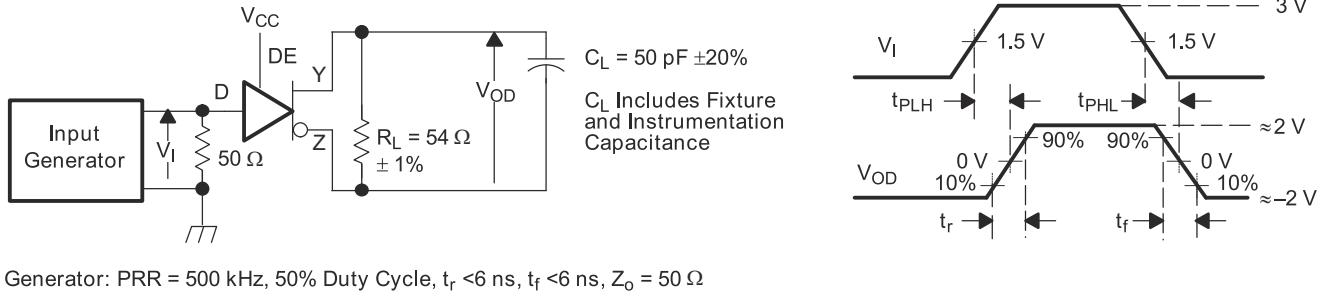


$C_L$  Includes Fixture and Instrumentation Capacitance

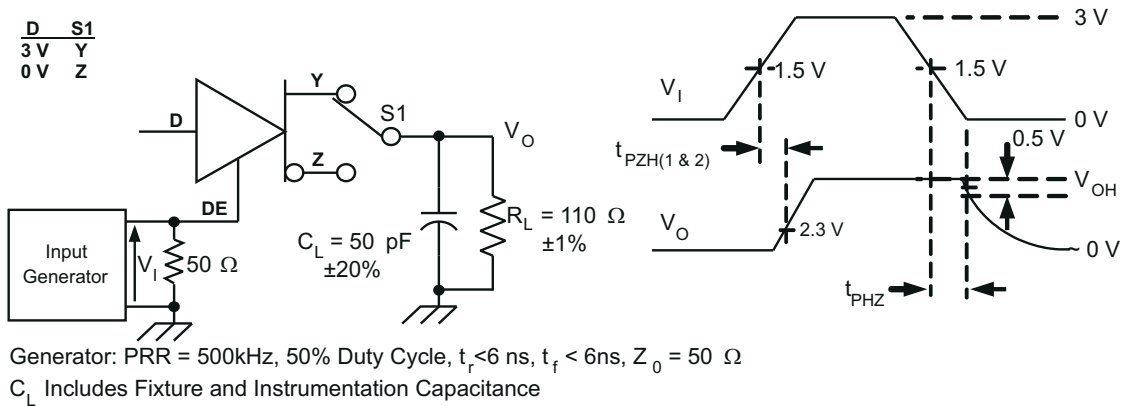
Input: PRR = 500 kHz, 50% Duty Cycle,  $t_r < 6\text{ns}$ ,  $t_f < 6\text{ns}$ ,  $Z_O = 50\ \Omega$

图 8-4. Test Circuit and Definitions for the Driver Common-Mode Output Voltage

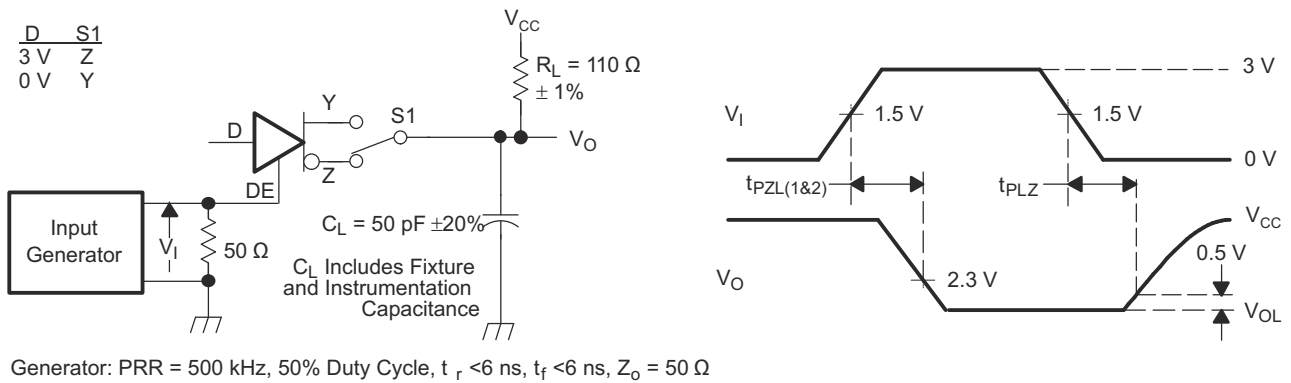




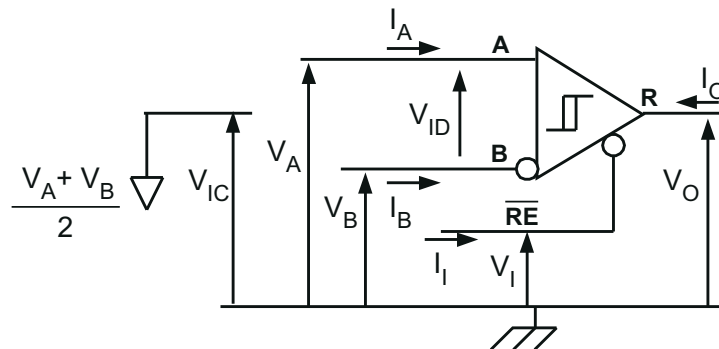
**图 8-5. Driver Switching Test Circuit and Voltage Waveforms**



**图 8-6. Driver High-Level Output Enable and Disable Time Test Circuit and Voltage Waveforms**



**图 8-7. Driver Low-Level Output Enable and Disable Time Test Circuit and Voltage Waveforms**



**图 8-8. Receiver Voltage and Current Definitions**

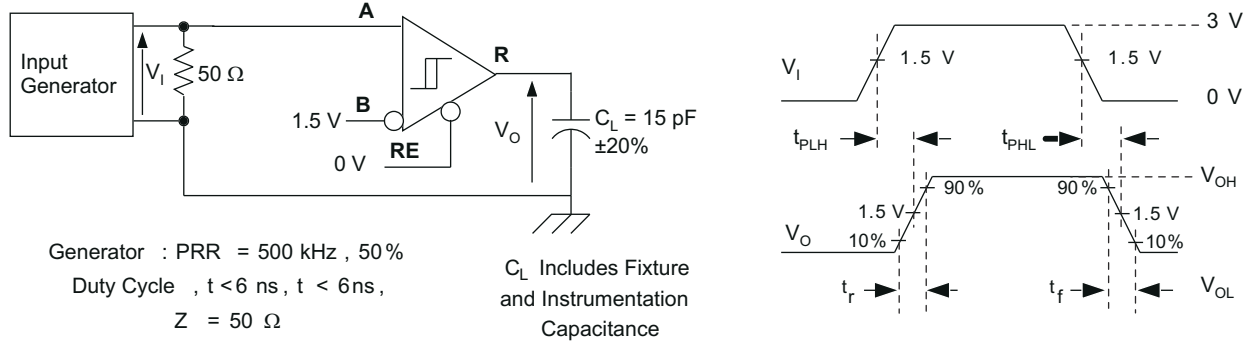


图 8-9. Receiver Switching Test Circuit and Voltage Waveforms

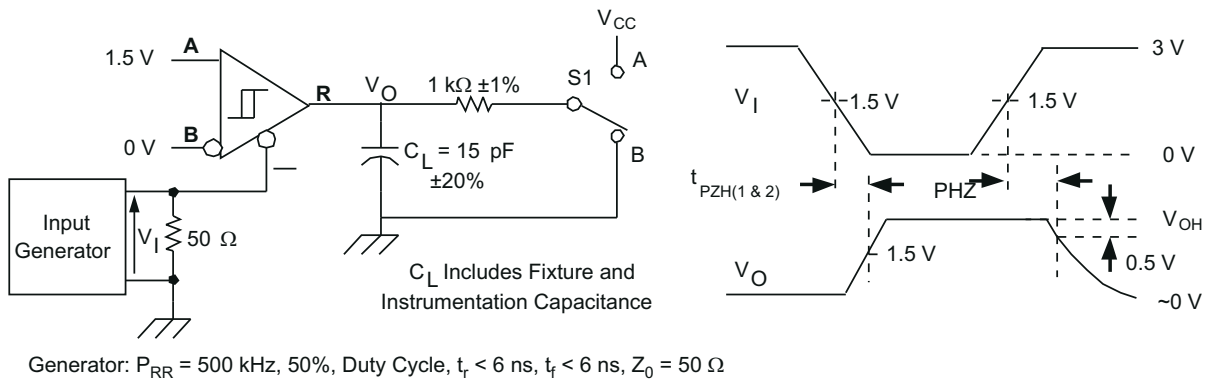


图 8-10. Receiver High-Level Enable and Disable Time Test Circuit and Voltage Waveforms

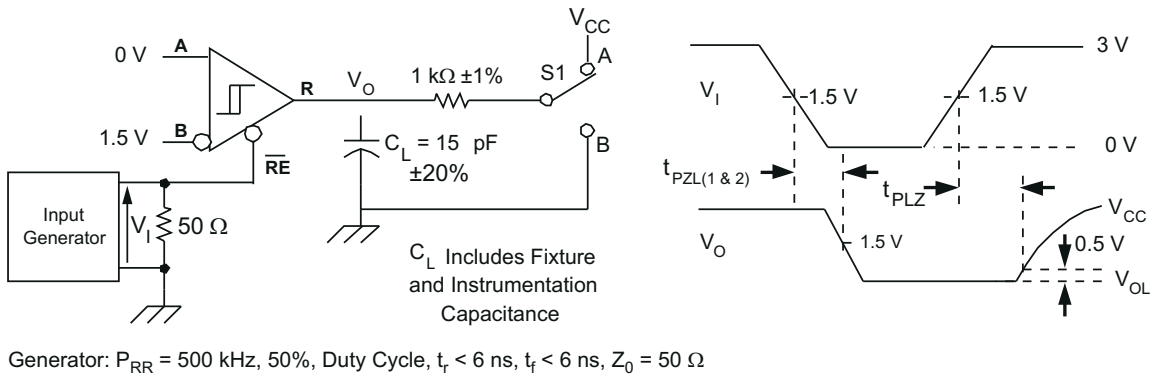


图 8-11. Receiver Low-Level Enable and Disable Time Test Circuit and Voltage Waveforms

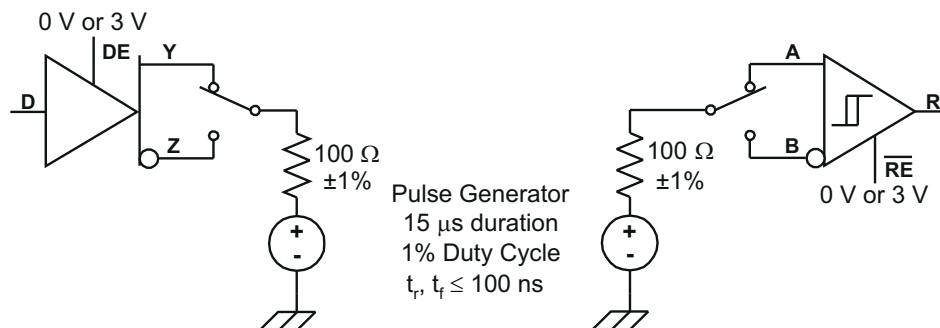
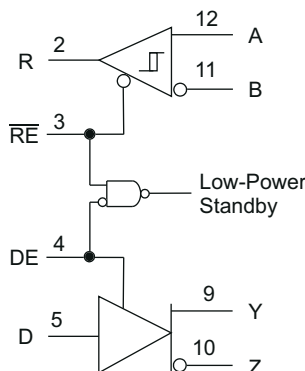


图 8-12. Test Circuit, Transient Overvoltage Test

## 9 Device Information

### 9.1 LI-Power Standby Mode

When both the driver and receiver are disabled ( $\overline{RE}$  high) the device is in standby mode. If the enable inputs are in this state for less than 60 ns, the device does not enter standby mode. This guards against inadvertently entering standby mode during driver/receiver enabling. Only when the enable inputs are held in this state for 300 ns or more, the device is assured to be in standby mode. In this low-power standby mode, most internal circuitry is powered down, and the supply current is typically less than 1 nA. When either the driver or the receiver is re-enabled, the internal circuitry becomes active.



**图 9-1. Low-Power Standby Logic Diagram**

If only the driver is re-enabled ( $DE$  transitions to high) the driver outputs are driven according to the  $D$  input after the enable times given by  $t_{PZH2}$  and  $t_{PZL2}$  in the driver switching characteristics. If the  $D$  input is open when the driver is enabled, the driver outputs default to  $A$  high and  $B$  low, in accordance with the driver failsafe feature.

If only the receiver is re-enabled ( $\overline{RE}$  transitions to low) the receiver output is driven according to the state of the bus inputs ( $A$  and  $B$ ) after the enable times given by  $t_{PZH2}$  and  $t_{PZL2}$  in the receiver switching characteristics. If there is no valid state on the bus the receiver responds as described in the failsafe operation section.

If both the receiver and driver are re-enabled simultaneously, the receiver output is driven according to the state of the bus inputs ( $A$  and  $B$ ) and the driver output is driven according to the  $D$  input. Note that the state of the active driver affects the inputs to the receiver. Therefore, the receiver outputs are valid as soon as the driver outputs are valid.

## 9.2 Function Tables

表 9-1. SN65HVD53, SN65HVD54, SN65HVD55  
 DRIVER

INPUTS		OUTPUTS	
D	DE	Y	Z
H	H	H	L
L	H	L	H
X	L or open	Z	Z
Open	H	L	H

表 9-2. SN65HVD53, SN65HVD54, SN65HVD55  
 RECEIVER

DIFFERENTIAL INPUTS $V_{ID} = V_{(A)} - V_{(B)}$	ENABLE RE	OUTPUT R
$V_{ID} \leq -0.2 \text{ V}$	L	L
$-0.2 \text{ V} < V_{ID} < -0.02 \text{ V}$	L	?
$-0.02 \text{ V} \leq V_{ID}$	L	H
X	H or open	Z
Open Circuit	L	H
Idle circuit	L	H
Short Circuit, $V_{(A)} = V_{(B)}$	L	H

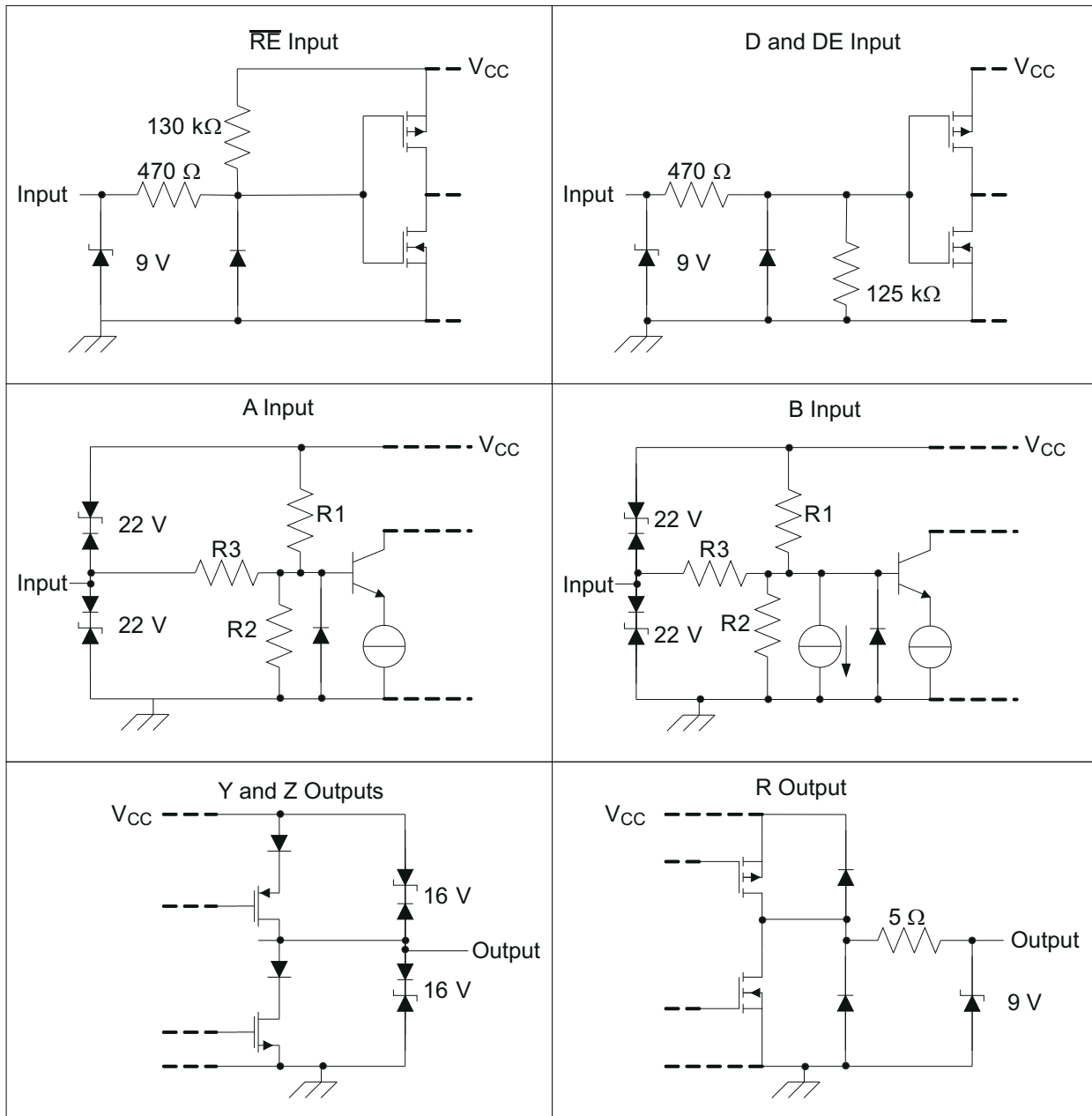
表 9-3. SN65HVD50, SN65HVD51, SN65HVD52  
 DRIVER

INPUT D	OUTPUTS	
	Y	Z
H	H	L
L	L	H
Open	L	H

表 9-4. SN65HVD50, SN65HVD51, SN65HVD52  
 RECEIVER

DIFFERENTIAL INPUTS $V_{ID} = V_{(A)} - V_{(B)}$	OUTPUT R
$V_{ID} \leq -0.2 \text{ V}$	L
$-0.2 \text{ V} < V_{ID} < -0.02 \text{ V}$	?
$-0.02 \text{ V} \leq V_{ID}$	H
Open Circuit	H
Idle circuit	H
Short Circuit, $V_{(A)} = V_{(B)}$	H

### 9.3 Equivalent Input and Output Schematic Diagrams



	R1/R2	R3
SN65HVD50, SN65HVD53	9 kΩ	45 kΩ
SN65HVD51, SN65HVD52, SN65HVD54, SN65HVD55	36 kΩ	180 kΩ

## 10 Application and Implementation

### 备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

### 10.1 Thermal Characteristics of IC Packages

$\theta_{JA}$  (**Junction-to-Ambient Thermal Resistance**) is defined as the difference in junction temperature to ambient temperature divided by the operating power.

$\theta_{JA}$  is not a constant and is a strong function of:

- the PCB design (50% variation)
- altitude (20% variation)
- device power (5% variation)

$\theta_{JA}$  can be used to compare the thermal performance of packages if the specific test conditions are defined and used. Standardized testing includes specification of PCB construction, test chamber volume, sensor locations, and the thermal characteristics of holding fixtures.  $\theta_{JA}$  is often misused when it is used to calculate junction temperatures for other installations.

TI uses two test PCBs as defined by JEDEC specifications. The low-k board gives *average* in-use condition thermal performance, and it consists of a single copper trace layer 25 mm long and 2-oz thick. The high-k board gives *best case* in-use condition, and it consists of two 1-oz buried power planes with a single copper trace layer 25 mm long and 2-oz thick. A 4% to 50% difference in  $\theta_{JA}$  can be measured between these two test cards

$\theta_{JC}$  (**Junction-to-Case Thermal Resistance**) is defined as difference in junction temperature to case divided by the operating power. It is measured by putting the mounted package up against a copper block cold plate to force heat to flow from die, through the mold compound into the copper block.

$\theta_{JC}$  is a useful thermal characteristic when a heatsink applied to package. It is *not* a useful characteristic to predict junction temperature because it provides pessimistic numbers if the case temperature is measured in a nonstandard system and junction temperatures are backed out. It can be used with  $\theta_{JB}$  in 1-dimensional thermal simulation of a package system.

$\theta_{JB}$  (**Junction-to-Board Thermal Resistance**) is defined as the difference in the junction temperature and the PCB temperature at the center of the package (closest to the die) when the PCB is clamped in a cold-plate structure.  $\theta_{JB}$  is only defined for the high-k test card.

$\theta_{JB}$  provides an overall thermal resistance between the die and the PCB. It includes a bit of the PCB thermal resistance (especially for BGA's with thermal balls) and can be used for simple 1-dimensional network analysis of package system, see [图 10-1](#).

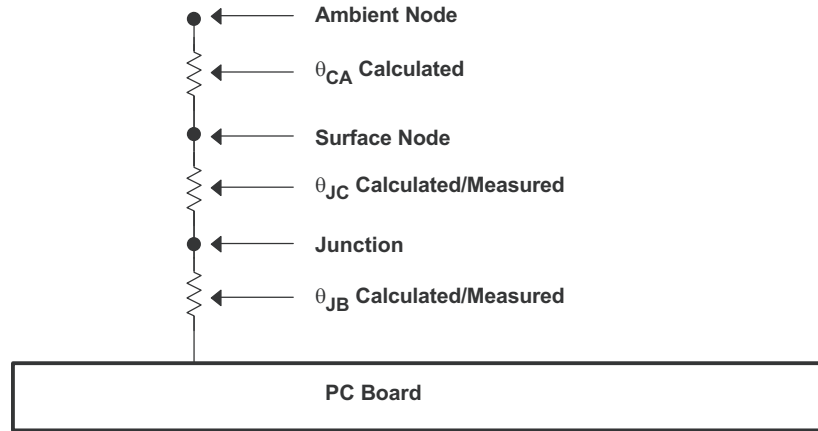


图 10-1. Thermal Resistance

## 11 Device and Documentation Support

### 11.1 接收文档更新通知

要接收文档更新通知，请导航至 [ti.com](http://ti.com) 上的器件产品文件夹。点击 [订阅更新](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

### 11.2 支持资源

TI E2E™ [支持论坛](#) 是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《[使用条款](#)》。

### 11.3 商标

TI E2E™ is a trademark of Texas Instruments.

所有商标均为其各自所有者的财产。

### 11.4 静电放电警告



静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

### 11.5 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

## 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN65HVD50D	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VP50	<a href="#">Samples</a>
SN65HVD50DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VP50	<a href="#">Samples</a>
SN65HVD51D	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VP51	<a href="#">Samples</a>
SN65HVD51DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VP51	<a href="#">Samples</a>
SN65HVD52D	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VP52	<a href="#">Samples</a>
SN65HVD52DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VP52	<a href="#">Samples</a>
SN65HVD53D	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65HVD53	<a href="#">Samples</a>
SN65HVD53DR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65HVD53	<a href="#">Samples</a>
SN65HVD54D	NRND	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65HVD54	
SN65HVD54DG4	NRND	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65HVD54	
SN65HVD54DR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65HVD54	<a href="#">Samples</a>
SN65HVD55D	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65HVD55	<a href="#">Samples</a>
SN65HVD55DR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65HVD55	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65HVD50DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65HVD51DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65HVD52DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65HVD53DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN65HVD54DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN65HVD55DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65HVD50DR	SOIC	D	8	2500	356.0	356.0	35.0
SN65HVD51DR	SOIC	D	8	2500	356.0	356.0	35.0
SN65HVD52DR	SOIC	D	8	2500	356.0	356.0	35.0
SN65HVD53DR	SOIC	D	14	2500	350.0	350.0	43.0
SN65HVD54DR	SOIC	D	14	2500	350.0	350.0	43.0
SN65HVD55DR	SOIC	D	14	2500	350.0	350.0	43.0

**TUBE**


\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
SN65HVD50D	D	SOIC	8	75	506.6	8	3940	4.32
SN65HVD51D	D	SOIC	8	75	506.6	8	3940	4.32
SN65HVD52D	D	SOIC	8	75	506.6	8	3940	4.32
SN65HVD53D	D	SOIC	14	50	505.46	6.76	3810	4
SN65HVD54D	D	SOIC	14	50	505.46	6.76	3810	4
SN65HVD54DG4	D	SOIC	14	50	505.46	6.76	3810	4
SN65HVD55D	D	SOIC	14	50	505.46	6.76	3810	4





D0008A

# PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed  $.006$  [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

# EXAMPLE BOARD LAYOUT

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE  
BASED ON .005 INCH [0.125 MM] THICK STENCIL  
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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